AP3D2R6CMT

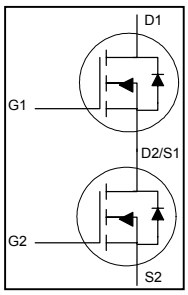
Halogen-Free Product

Advanced Power Electronics Corp.

ASYMMETRIC DUAL N-CHANNEL

ENHANCEMENT MODE POWER MOSFET

- ▼ **Simple Drive Requirement**
- ▼ **Easy for DC/DC Buck Converter Application**
- ▼ **RoHS Compliant & Halogen-Free**

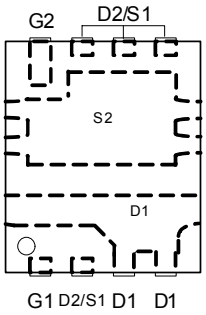


CH-1	BV_{DSS}	30V
	$R_{DS(ON)}$	8.2mΩ
CH-2	BV_{DSS}	30V
	$R_{DS(ON)}$	2.4mΩ

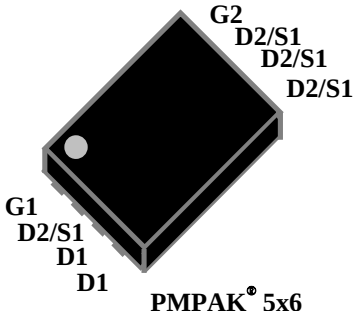
Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The control MOSFET (CH-1) and synchronous MOSFET (CH-2) co-package for synchronous buck converters. The package provide optimal efficiency with low stray inductance and very low on-resistance.



PMPAK 5x6



PMPAK® 5x6

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating		Units
		CH-1	CH-2	
V_{DS}	Drain-Source Voltage	30	30	V
V_{GS}	Gate-Source Voltage	+20 / -12	+20 / -12	V
I_D@T_C=25℃	Drain Current (Silicon Limited)	42	100	A
I_D@T_A=25℃	Drain Current[3] , V_{GS} @ 10V	12.2	24.3	A
I_D@T_A=70℃	Drain Current[3] , V_{GS} @ 10V	9.8	19.4	A
I_{DM}	Pulsed Drain Current[1]	40	75	A
P_D@T_A=25℃	Total Power Dissipation[3]	2.08	2.27	W
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Thermal Data

Symbol	Parameter	Rating		Units
		CH-1	CH-2	
Rthj-c	Maximum Thermal Resistance, Junction-case	5	3	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	60	55	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[4]	130	120	℃/W

CH-1 Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=14A	-	-	8.2	mΩ
		V_{GS}=4.5V, I_D=7A	-	-	13	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	2.5	V
g_{fs}	Forward Transconductance	V_{DS}=5V, I_D=14A	-	33	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V, V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=+20V, V_{DS}=0V	-	-	100	nA
Q_g	Total Gate Charge	I_D=7A	-	7	11.2	nC
Q_{gs}	Gate-Source Charge	V_{DS}=15V	-	4	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	1	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V	-	9	-	ns
t_r		I_D=14A	-	48	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3Ω	-	17	-	ns
t_f	Fall Time	V_{GS}=10V	-	2	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	1200	1920	pF
C_{oss}	Output Capacitance	V_{DS}=15V	-	270	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	10	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1	2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=14A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time	I_S=14A, V_{GS}=0V	-	17	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	9	-	nC

CH-2 Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=20A	-	-	2.4	mΩ
		V_{GS}=4.5V, I_D=12A	-	-	3	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1.1	-	2.5	V
g_{fs}	Forward Transconductance	V_{DS}=5V, I_D=20A	-	86	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V, V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=+20V, V_{DS}=0V	-	-	100	nA
Q_g	Total Gate Charge	I_D=12A	-	30	48	nC
Q_{gs}	Gate-Source Charge	V_{DS}=15V	-	11	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	6.5	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V	-	11	-	ns
t_r	Rise Time	I_D=20A	-	64	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3Ω	-	50	-	ns
t_f	Fall Time	V_{GS}=10V	-	14	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	4300	6880	pF
C_{oss}	Output Capacitance	V_{DS}=15V	-	1050	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	34	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.7	3.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=20A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time	I_S=20A, V_{GS}=0V	-	35	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	29	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board, on steady-state

4.Surface mounted on Min. copper pad of FR4 board, on steady-state

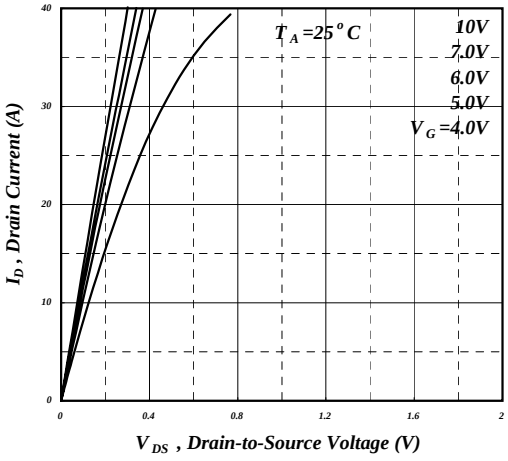


Fig 1. Typical Output Characteristics

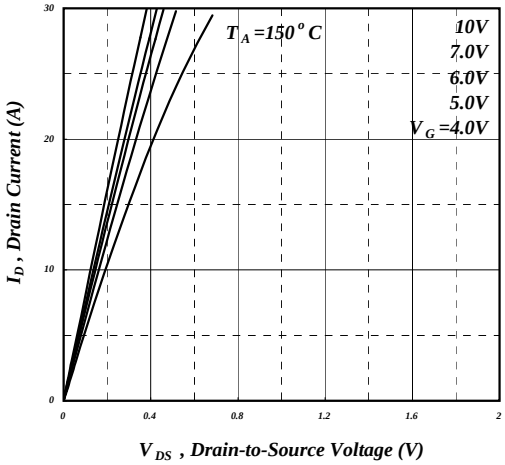


Fig 2. Typical Output Characteristics

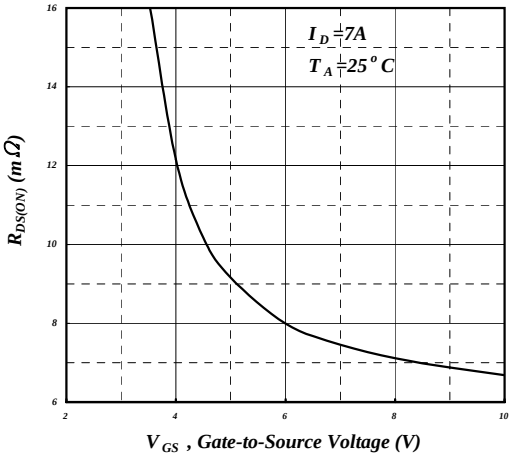


Fig 3. On-Resistance v.s. Gate Voltage

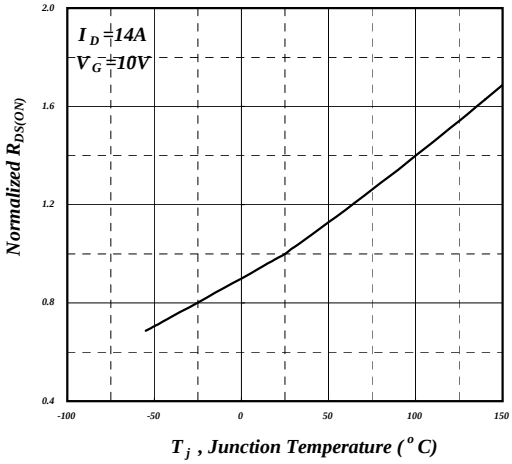


Fig 4. Normalized On-Resistance v.s. Junction Temperature

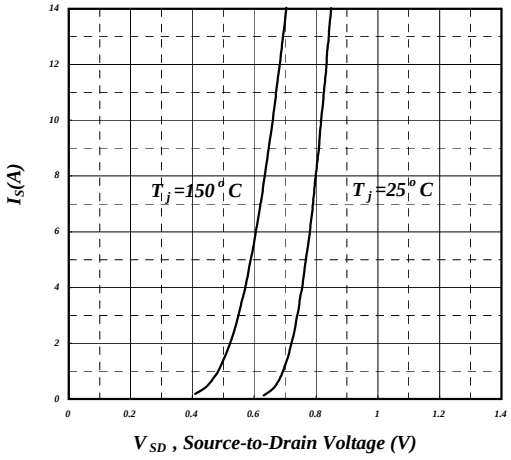


Fig 5. Forward Characteristic of Reverse Diode

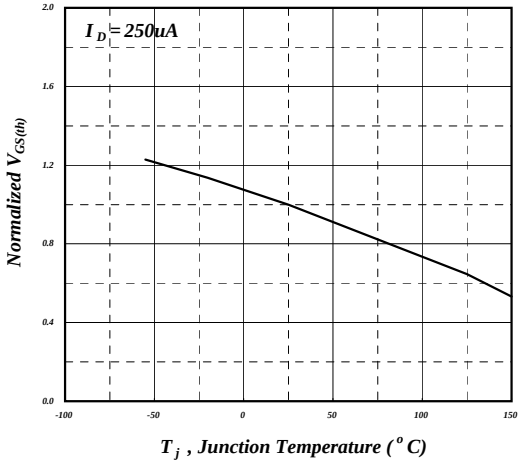


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

Channel-1

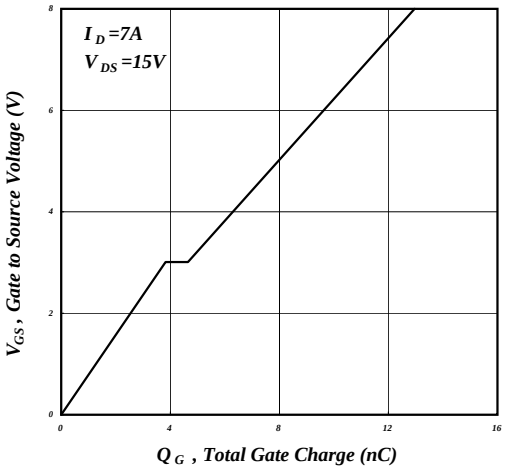


Fig 7. Gate Charge Characteristics

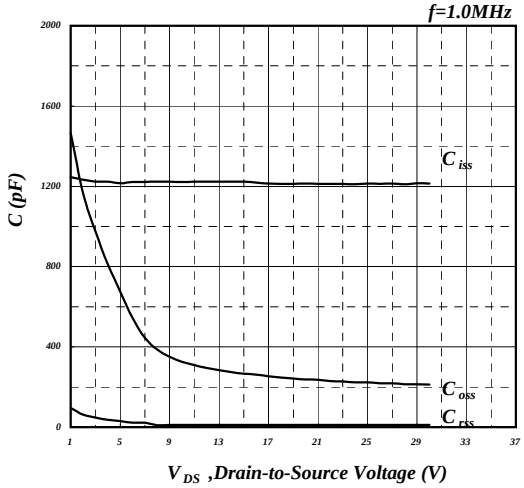


Fig 8. Typical Capacitance Characteristics

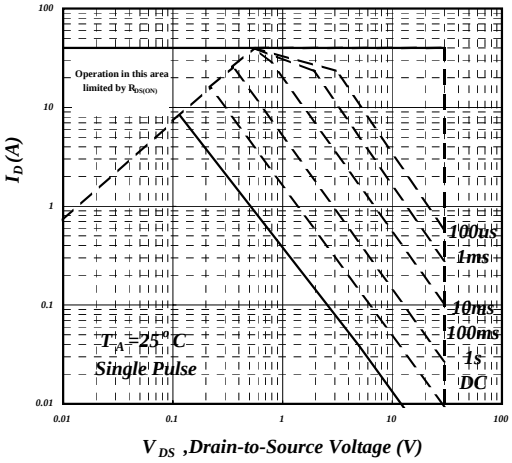


Fig 9. Maximum Safe Operating Area

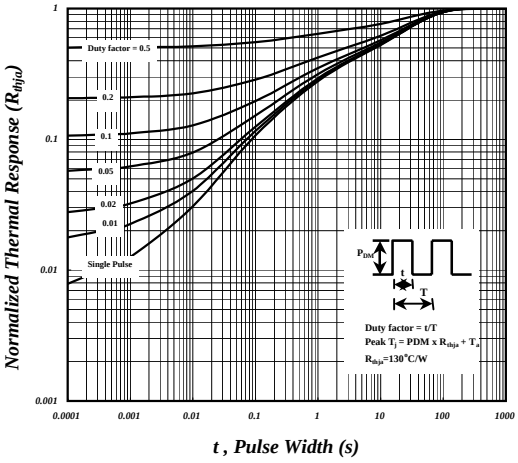


Fig 10. Effective Transient Thermal Impedance

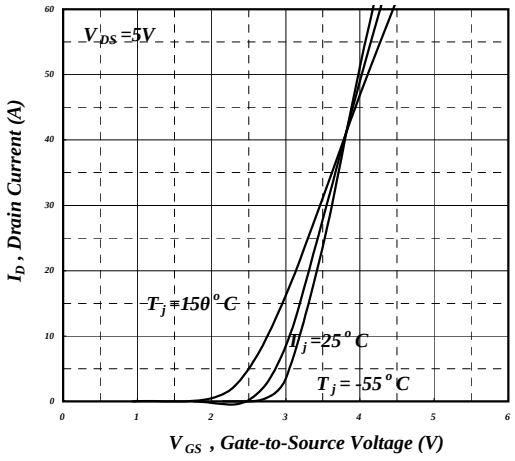


Fig 11. Transfer Characteristics

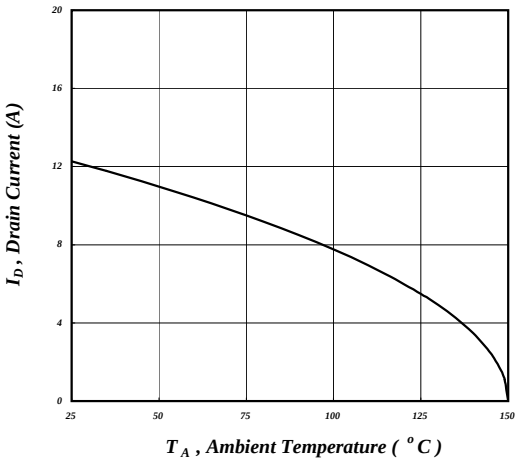


Fig 12. Drain Current v.s. Ambient Temperature

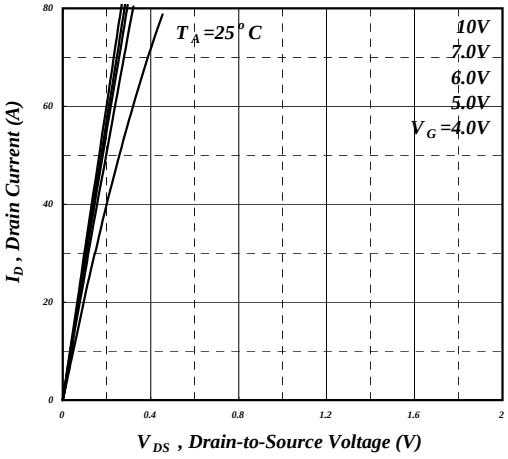


Fig 1. Typical Output Characteristics

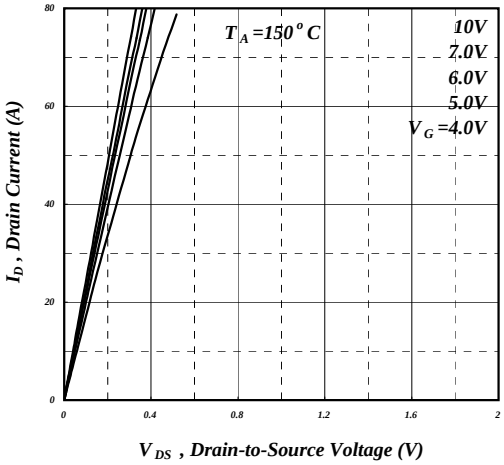


Fig 2. Typical Output Characteristics

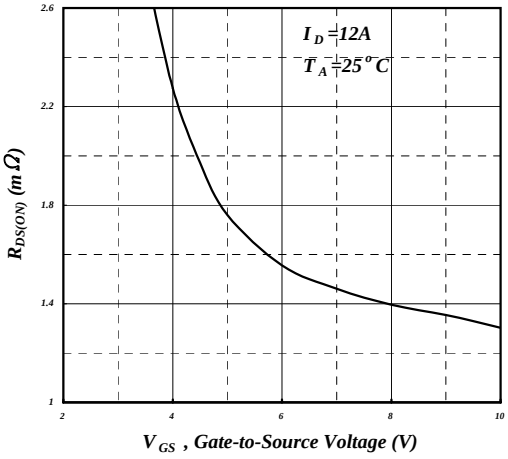


Fig 3. On-Resistance v.s. Gate Voltage

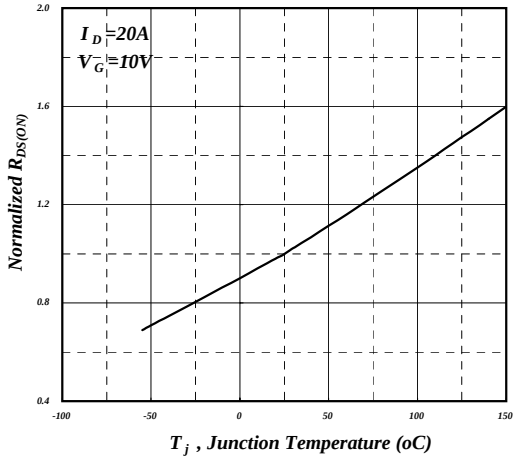


Fig 4. Normalized On-Resistance v.s. Junction Temperature

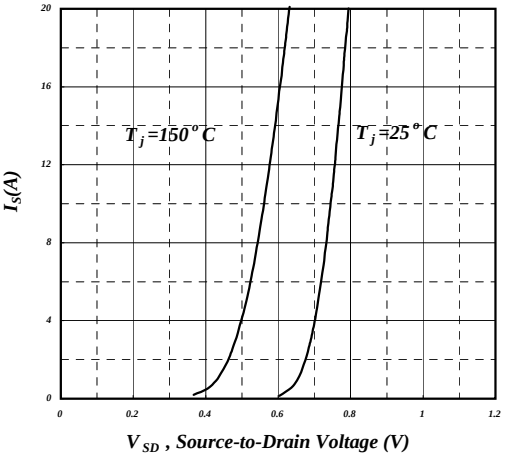


Fig 5. Forward Characteristic of Reverse Diode

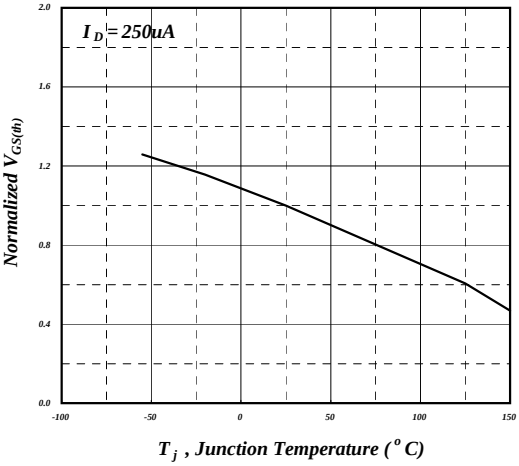


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

Channel-2

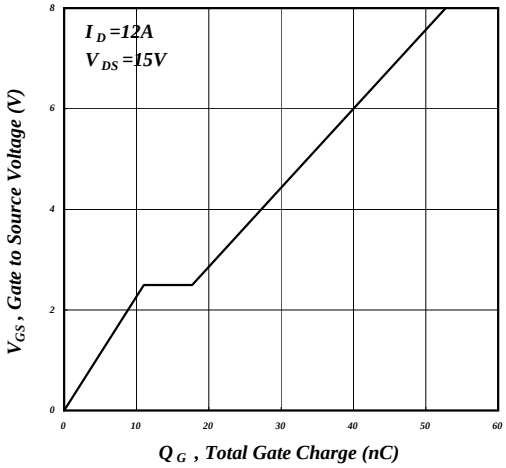
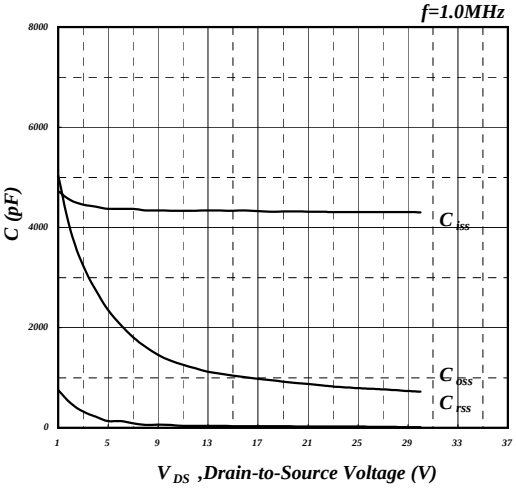


Fig 7. Gate Charge Characteristics



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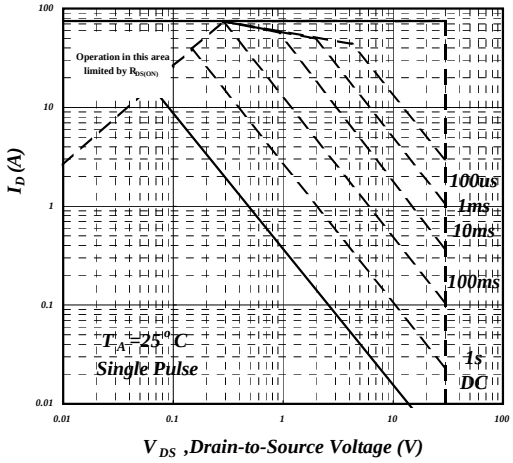

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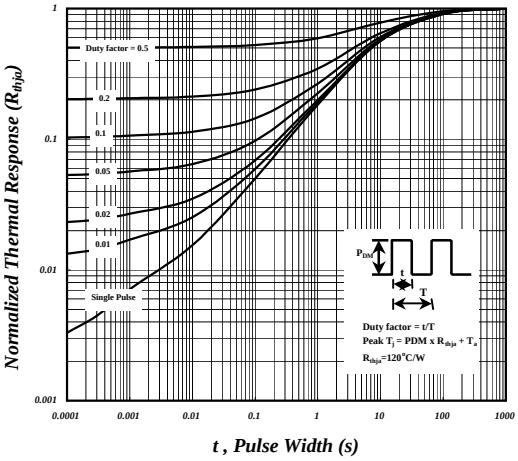

Fig 10. Effective Transient Thermal Impedance

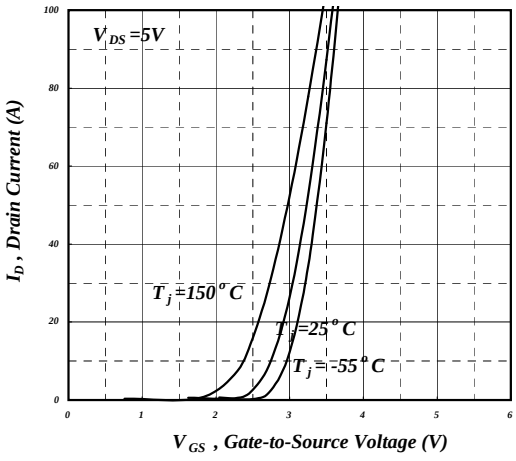

Fig 11. Transfer Characteristics

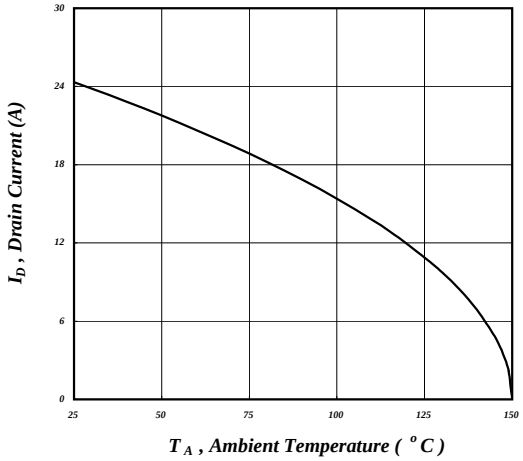

Fig 12. Drain Current v.s. Ambient Temperature

MARKING INFORMATION